

<b>Notice of References Cited</b>	Application/Control No. 09/852,999	Applicant(s)/Patent Under Reexamination MEILING ET AL.	
	Examiner Steven H. Rao	Art Unit 2814	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,634,605	06-1997	Rubel et al.	248/228.1
	C	US-5,776,819	07-1998	Mahan et al.	438/482
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	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.